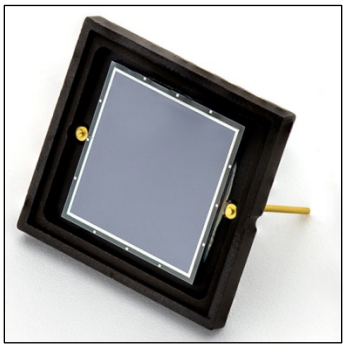
Electron Detection 100 mm^2 — AXUV100G



FEATURES

- Ideal for Electron Detection
- Large Detection Area
- 100% Internal QE
- Protective Cover Plate[3]

Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	100 mm x 100 mm		100		mm^2
Responsivity	@ 254 mm, V_R = 0 V	0.07	0.08	0.09	A/W
Shunt Resistance, Rsh	V_B = ± 10 mV	20			M-ohm
Reverse Breakdown Voltage, V_R	I_R = 1 µA	5	10		Volts
Capacitance, C	V_R = 0 V		10	44	nF
Rise Time	V_R = 0 V, R_L = 50 Ω			10	usec

Thermal Parameters

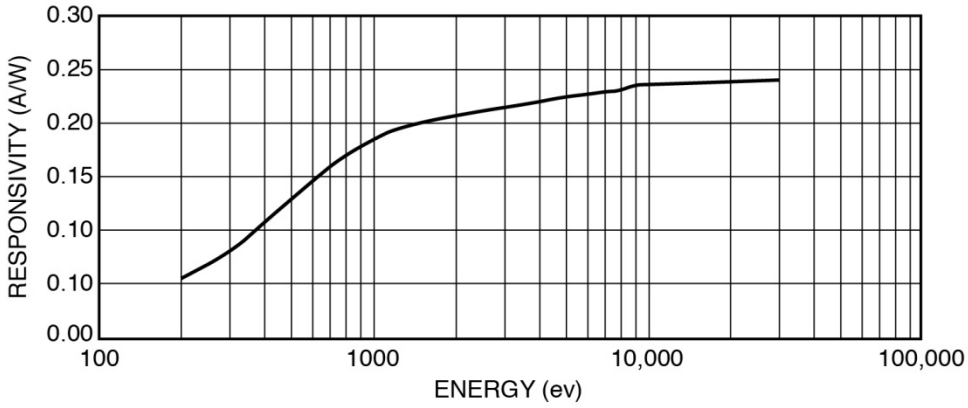
Storage and Operating Temperature Range	
Ambient[1]	-10 ° to 40 °C
Nitrogen or Vacuum	-20 °C to 80 °C
Maximum Junction Temperature	70 °C
Lead Soldering Temperature[2]	260 °C

[1] Temperatures exceeding these parameters may create oxide growth on the active area.
Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

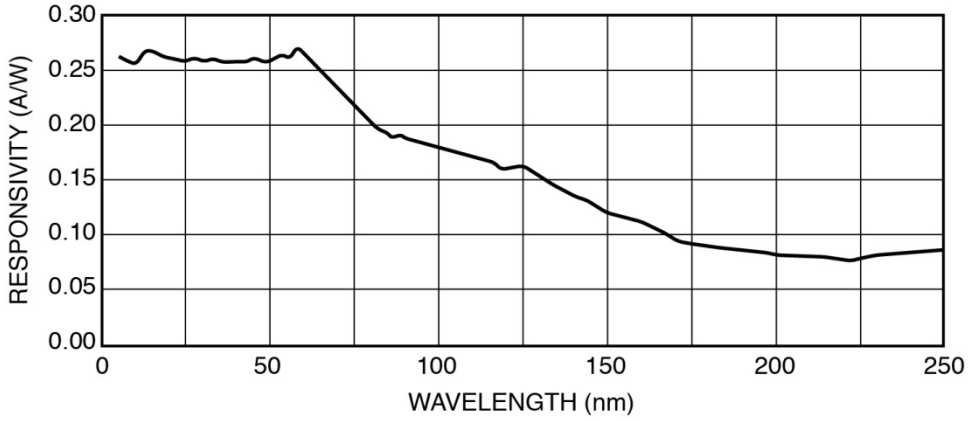
[2] 0.080" from case for 10 seconds.

[3] Shipped with temporary cover to protect the photodiode and wire bonds.
Review the Application Note, “Handling Precautions for AXUV, SXUV, and UVG Detectors”, prior to removing cover.

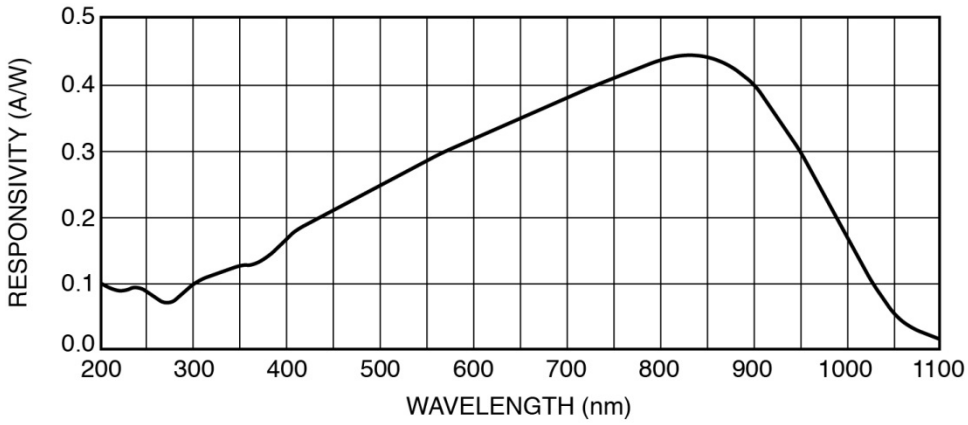
Typical Electron Response



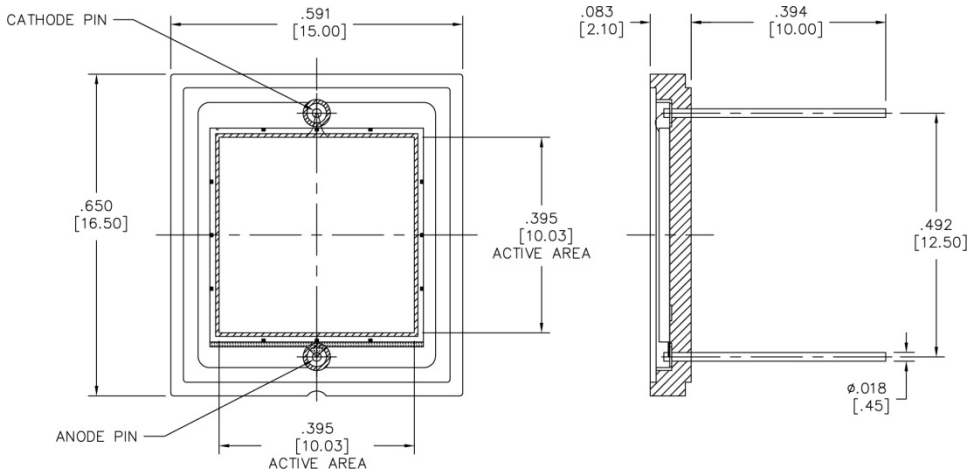
Typical EUV-UV Photon Response



Typical UV-VIS-NIR Photon Responsivity



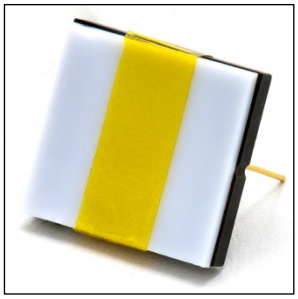
Package Information



Dimensions are in inch [metric] units.

Ordering Information

ODD-AXU-010	Large Photodiode Ideal for Radiation Detection Shipped with Protective Cover



Specifications are subject to change without prior notice.